

SANGDEST MICROELECTRONICS

Technical Data Data Sheet N0990, Rev. E

403CMQ SERIES SCHOTTKY RECTIFIER

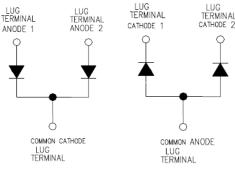
Applications:

- High current switching power supply Plating power supply Free-Wheeling diodes
- Reverse battery protection
 Converters
 UPS System
 Welding

Features:

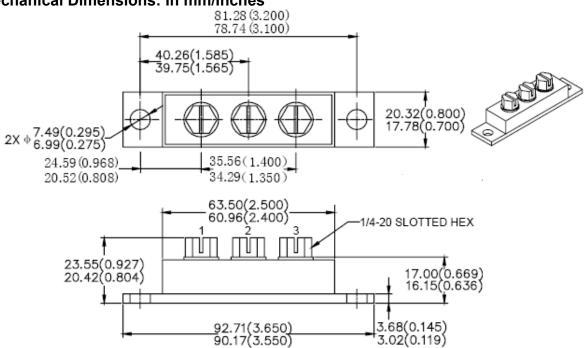
- 175 ℃ T_J operation
- Center tap module
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Product contain Pb
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Mechanical Dimensions: In mm/Inches



403CMQ080

403CMQ080R



Please Note: Suffix "R" Denotes For Reversed Polarity

PRM4 (Isolated)

MARKING, MOLDING RESIN Marking for 403CMQ080/R, 1st row SS YYWWL, 2nd row 403CMQ080/403CMQ080R Where YY is the manufacture year WW is the manufacture week code L is the wafer's Lot Number Molding resin Epoxy resin UL: 94V-0

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Technical Data Data Sheet N0990, Rev. E Maximum Ratings:

Characteristics	Symbol	Condition		Max.	Units	
Peak Inverse Voltage	V _{RWM}	-	80	403CMQ080/R	V	
			100	403CMQ100/R		
Average Forward Current	I _{F(AV)}	50% duty cycle @T _C =85°C,	200	per leg	А	
		rectangular wave form	400	per device		
Peak One Cycle Non- Repetitive Surge Current (per leg)	I _{FSM}	8.3 ms, half Sine pulse	3960		A	
Non-Repetitive Avalanche Energy(peg leg)	E _{AS}	T _J =25℃,I _{AS} =1A,L=30mH	15		mJ	
Repetitive Avalanche Current(peg leg)	I _{AR}	Current decaying linearly to zero in 1 μ sec Frequency limited by T _J max. V _A =1.5×V _R typical	1		A	

Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Forward Voltage Drop (per leg) *	V_{F1}	@ 200A, Pulse, T _J = 25 °C @ 400A, Pulse, T _J = 25 °C	0.83 0.97	V
	V_{F2}	@ 200A, Pulse, T _J = 125 °C @ 400A, Pulse, T _J = 125 °C	0.69 0.82	V
Reverse Current (per leg) *	I _{R1}	$@V_R = rated V_R T_J = 25 \circ C$	6	mA
	I _{R2}	$@V_R$ = rated V _R T _J = 125 °C	140	mA
Junction Capacitance (per leg)	C _T	@V _R = 5V, T _C = 25 °C f _{SIG} = 1MHz	5500	pF
Typical Series Inductance (per leg)	Ls	Measured lead to lead 5 mm from package body	5.0	nH
Max. Voltage Rate of Change	dv/dt	-	10,000	V/μs

* Pulse Width < 300µs, Duty Cycle <2%

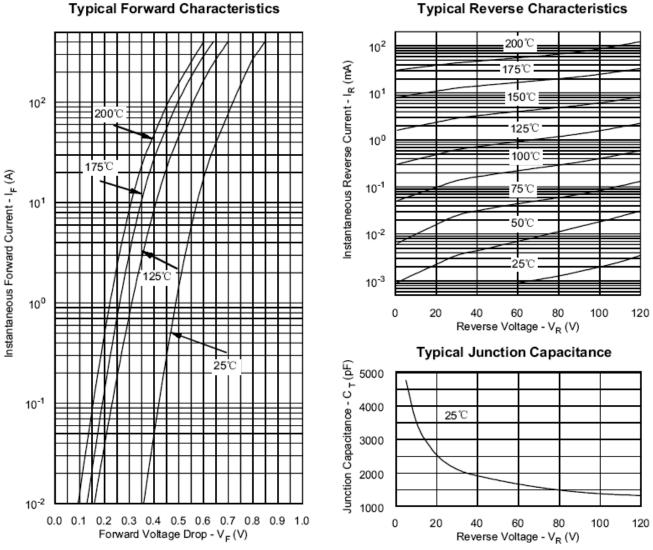
Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specifi	Units			
Junction Temperature	TJ	-	-55 to	°C			
Storage Temperature	T _{stg}	-	-55 to	°C			
Maximum Thermal Resistance Junction to Case (per leg)	R _{θJC}	DC operation	0.40		°C/W		
Maximum Thermal Resistance Junction to Case (per package)	$R_{ ext{ heta}JC}$	DC operation	0.20		°C/W		
Typical Thermal Resistance, case to Heat Sink	$R_{ ext{ heta}cs}$	Mounting surface, smooth and greased	0.10		°C/W		
Mounting Torque	Тм	-	Mounting Torque Terminal Torque	24(min) 35(max) 35(min) 46(max)	Kg-cm		
Approximate Weight	wt	-	79		g		
Case Style	PRM4 Isolated						

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